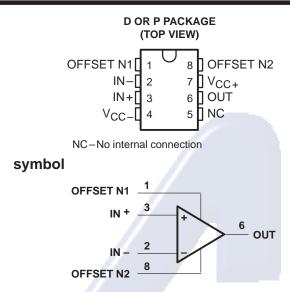
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- Low Noise
- **No External Components Required**
- **Replaces Chopper Amplifiers at a Lower** Cost
- **Single-Chip Monolithic Fabrication**
- Wide Input Voltage Range 0 to  $\pm$ 14 V Typ
- Wide Supply Voltage Range  $\pm$ 3 V to  $\pm$ 18 V
- Essentially Equivalent to Fairchild µA714 **Operational Amplifiers**
- **Direct Replacement for PMI OP07C and** • OP07D



#### description

These devices represent a breakthrough in operational amplifier performance. Low offset and long-term stability are achieved by means of a low-noise, chopperless, bipolar-input-transistor amplifier circuit. For most applications, external components are not required for offset nulling and frequency compensation. The true differential input, with a wide input voltage range and outstanding common-mode rejection, provides maximum flexibility and performance in high-noise environments and in noninverting applications. Low bias currents and extremely high input impedances are maintained over the entire temperature range. The OP07 is unsurpassed for low-noise, high-accuracy amplification of very low-level signals.

These devices are characterized for operation from 0°C to 70°C.

	PACKAGED DEVICES						
T <sub>A</sub> AT 25°C		SMALL OUTLINE (D)	PLASTIC DIP (P)	CHIP FORM (Y)			
0°C to 70°C	150 μV	OP07CD OP07DD	OP07CP OP07DP	OP07Y			



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.

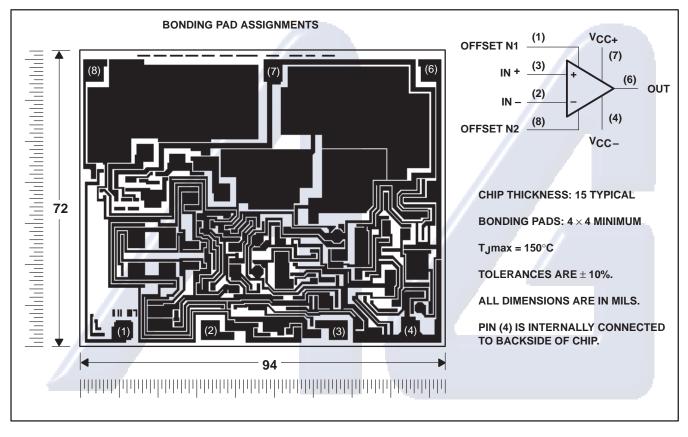


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#### **OP07Y** chip information

These chips, properly assembled, display characteristics similar to the OP07. Thermal compression or ultrasonic bonding may be used on the doped-aluminum bonding pads. Chips may be mounted with conductive epoxy or a gold-silicon preform.

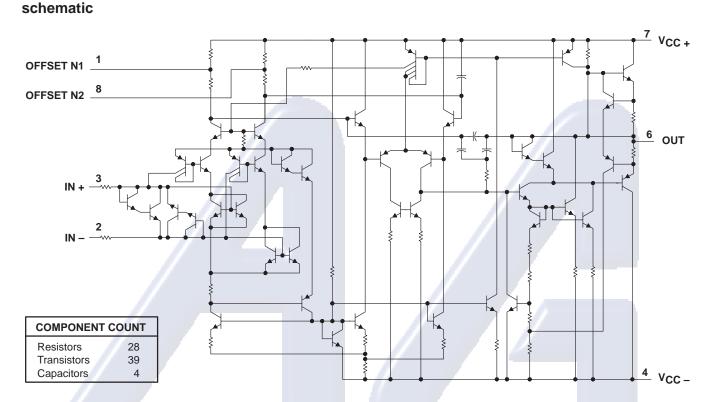


# Electrónica S.A. de C.V.



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#### absolute maximum ratings over operating free-air temperature range (unless otherwise noted)

Supply voltage, $V_{CC+}$ (see Note 1)			
Supply voltage, V <sub>CC</sub>			
Differential input voltage (see Note 2) .			
Input voltage, VI (either input, see Note	3)		 ±22 V
Duration of output short circuit (see Note	e 4)		 unlimited
Continuous total dissipation at (or below			
Operating free-air temperature range, T			
Storage temperature range		,	 –65°C to 150°C
Lead temperature 1,6 mm (1/16 inch) fr	om case for 10	) seconds	 260°C

NOTES: 1. All voltage values, unless otherwise noted, are with respect to the midpoint between V<sub>CC+</sub> and V<sub>CC-</sub>.

2. Differential voltages are at IN+ with respect to IN-.

3. The magnitude of the input voltage must never exceed the magnitude of the supply voltage or 15 V, whichever is less.

- 4. The output may be shorted to ground or either power supply.
- 5. For operation above 64°C free-air temperature, derate the D package to 464 mW at 70°C at the rate of 5.8 mW/°C.

#### recommended operating conditions

		MIN	MAX	UNIT
Supply voltage, V <sub>CC<math>\pm</math></sub>		±3	±18	V
Common-mode input voltage, VIC	$V_{CC\pm} = \pm 15 V$	-13	13	V
Operating free-air temperature, TA		0	70	°C



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#### electrical characteristics at specified free-air temperature, $V_{CC} \pm = \pm 15$ V (unless otherwise noted)

						OP07C			OP07D			
	PARAMETER	TEST CO	NDITIONS <sup>†</sup>	TA	MIN	TYP	MAX	MIN	TYP	MAX	UNIT	
Vie	Input offset voltage	$V_{O} = 0,$	Rs = 50 Ω	25°C		60	150		60	150	μV	
VIO	input onset voltage	VO = 0,	KS = 50.22	0°C to 70°C		85	250	1	85	250	μν	
ανιο	Temperature coefficient of input offset voltage	V <sub>O</sub> = 0,	R <sub>S</sub> = 50 Ω	0°C to 70°C		0.5	1.8		0.7	2.5	μV/°C	
	Long-term drift of input offset voltage	See Note 6				0.4			0.5		μV/mo	
	Offset adjustment range	R <sub>S</sub> = 20 kΩ,	See Figure 1	25°C		±4			±4	_	mV	
10	Input offset current			25°C	1	0.8	6		0.8	6	nA	
U	input onset current			0°C to 70°C		1.6	8		1.6	8	8	
αlio	Temperature coefficient of input offset current			0°C to 70°C		12	50	1	12	50	pA/°C	
lun.	Input bias current			25°C		±1.8	±7	1	±2	±12	nA l	
İΒ	input bias current			0°C to 70°C		±2.2	±9		±3	±14		
αlib	Temperature coefficient of input bias current			0°C to 70°C		18	50		18	50	pA/°C	
V/	Common-mode input voltge range			25°C	±13	±14		±13	±14		V	
VICR	Common-mode input voltge range			0°C to 70°C	±13	±13.5		±13	±13.5			
	Peak output voltage	R <sub>L</sub> ≥ 10 kΩ			±12	±13		±12	±13		- v	
Vом		$R_L \ge 2 k\Omega$		25°C	±11.5	±12.8		±11.5	±12.8			
V OIVI		$R_L \ge 1 \ k\Omega$				±12			±12			
		R <sub>L</sub> ≥2 kΩ		0°C to 70°C	±11	±12.6		±11	±12.6			
		$\begin{array}{l} V_{CC} \pm = \pm 3 \text{ V}, \\ R_L \geq 500 \text{ k}\Omega \end{array}$	$V_{O} = \pm 0.5 V_{O}$	25°C	100	400			400			
AVD	Large-signal differential voltage amplification	$V_{O} = \pm 10 V_{0}$	R <sub>1</sub> = 2 kΩ	25°C	120	400		120	400		V/mV	
		VO = ± 10 V,	NL - 2 K32	0°C to 70°C	100	400		100	400			
В <sub>1</sub>	Unity-gain bandwidth			25°C	0.4	0.6		0.4	0.6		MHz	
ri	Input resistance			25°C	8	33		7	31		MΩ	
CMRR	Common-mode rejection ratio	$V_{IC} = \pm 13 V$	Rs = 50 Ω	25°C	100	120		94	110		dB	
CIVILAT	Common-mode rejection ratio	VIC = ± 13 V,	NS = 30 32	0°C to 70°C	97	120	_	94	106		, ub	
kovo	Supply voltage sensitivity ( $\Delta V_{IO}/\Delta V_{CC}$ )	$V_{CC\pm} = \pm 3 V$	to ±18 V,	25°C		7	32		7	32	μV/V	
ksvs	Cuppin voltage sensitivity (AvID/AvCC)	R <sub>S</sub> = 50 Ω		0°C to 70°C		10	51		10	51	51 <sup>µ0/0</sup>	
		V <sub>O</sub> = 0,	No load			80	150		80	150		
PD	Power dissipation	$V_{CC\pm} = \pm 3 V,$ No load	$V_{O} = 0,$	25°C		4	8		4	8	mW	

<sup>†</sup> All characteristics are measured under open-loop conditions with zero common-mode input voltage unless otherwise noted. NOTE 6: Since long-term drift cannot be measured on the individual devices prior to shipment, this specification is not intended to be a warranty. It is an engineering estimate of the

averaged trend line of drift versus time over extended periods after the first thirty days of operation.

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# OP07C, OP07D, OP07Y PRECISION OPERATIONAL AMPLIFIERS

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## operating characteristics, V\_{CC\pm} = $\pm 15$ V, T\_A = 25°C

PARAMETER		TEST	OP07C			(	UNIT		
	PARAMETER	CONDITIONS <sup>†</sup>	MIN	TYP	MAX	MIN	TYP	MAX	UNIT
Vn	Equivalent input noise voltage	f = 10 Hz		10.5			10.5		
		f = 100 Hz		10.2			10.3		nV/√Hz
		f = 1 kHz		9.8			9.8	1	
V <sub>N(PP)</sub>	Peak-to-peak equivalent input noise voltage	f = 0.1 Hz to 10 Hz		0.38			0.38		μV
	Equivalent input noise current	f = 10 Hz		0.35			0.35		
In		f = 100 Hz		0.15		1	0.15		pA/√Hz
		f = 1 kHz		0.13			0.13		
I <sub>N(PP)</sub>	Peak-to-peak equivalent input noise current	f = 0.1 Hz to 10 Hz		15	/		15		pА
SR	Slew rate	$R_L \ge 2 k\Omega$		0.3			0.3		V/µs

<sup>†</sup> All characteristics are measured under open-loop conditions with zero common-mode input voltage unless otherwise noted.

## electrical characteristics, V\_{CC\pm} = $\pm 15$ V, T\_A = 25°C (unless otherwise noted)

DADAMETED			TEST CONDITIONST			OP07Y			
	PARAMETER	TEST CONDITIONS <sup>†</sup>			MIN	TYP	MAX	UNIT	
VIO	Input offset voltage	R <sub>S</sub> = 50 Ω			1	60	150	μV	
	Long-term drift of input offset voltage	See Note 6	5		/	0.5		μV/mo	
	Offset adjustment range	$R_{S} = 20 k\Omega$	2, See Figure 1			±4		mV	
IIO	Input offset current					0.8	6	nA	
IIB	Input bias current					±2	±12	nA	
VICR	Common-mode input voltage range				±13	±14		V	
		R <sub>L</sub> ≤ 10 kΩ	2		±12	±13			
Vом	Peak output voltage	$R_L \le 2 k\Omega$			±11.5	±12.8		V	
-		$R_L \le 1 \ k\Omega$				±12			
A		$V_{CC\pm} = \pm 3$	$3 \text{ V}, \text{ V}_{\text{O}} = \pm 0.5 \text{ V}, \text{ R}$	L ≤ 500 kΩ		400			
AVD	Large-signal differential voltage amplification	$V_{O} = \pm 10^{\circ}$	V, $R_L = 2 k\Omega$		120	400			
В <sub>1</sub>	Unity-gain bandwidth				0.4	0.6		MHz	
rj	Input resistance				7	31		MΩ	
CMRR	Common-mode input resistance	$V_{IC} = \pm 13$	V, R <sub>S</sub> = 50 Ω		94	110	1	dB	
ksvs	Supply-voltage rejection ratio ( $\Delta V_{CC} / \Delta V_{IO}$ )	$V_{CC\pm} = \pm 3$	3 V to ±18 V, R	s = 50 Ω		/ 7	32	μV/V	
D-	Power dissinction	V <sub>O</sub> = 0,	No load			80	150	MΩ	
PD	Power dissipation	$V_{CC\pm} = \pm 3$	$3 V, V_0 = 0, N_0$	o load		4	8	10122	

NOTE 6: Since long-term drift cannot be measured on the individual devices prior to shipment, this specification is not intended to be a warranty. It is an engineering estimate of the averaged trend line of drift versus time over extended periods after the first thirty days of operation.



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## operating characteristics, V\_{CC\pm} = $\pm 15$ V, T\_A = 25°C

	PARAMETER	TEST CONDITIONS <sup>†</sup>	C		UNIT			
	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT		
		f = 10 Hz		10.5		nV/√Hz		
Vn	Equivalent input noise voltage	f = 1 kHz		10.3				
		f = 0.1 Hz to 10 Hz		9.8				
V <sub>N(PP)</sub>	Peak-to-peak equivalent input noise voltage	f = 0.1 Hz to 10 Hz		0.38		μV		
	Equivalent input noise current	f = 10 Hz		0.35				
I <sub>n</sub>		f = 100 Hz		0.15		pA/√Hz		
		f = 1 kHz		0.13				
I <sub>N(PP)</sub>	Peak-to-peak equivalent input noise current	f = 0.1 Hz to 10 Hz		15		pА		
SR	Slew rate	$R_L = 2 k\Omega$	1	0.3		V/µs		

<sup>†</sup> All characteristics are measured under open-loop conditions with zero common-mode input voltage unless otherwise noted.

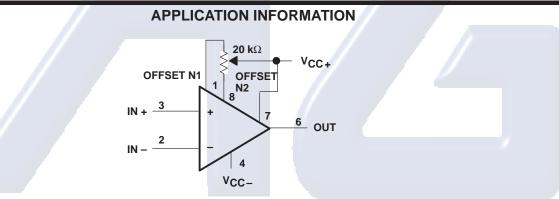


Figure 1. Input Offset Voltage Null Circuit





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